

NPN High Voltage Amplifier

This device is designed for application as a video output to drive color CRT and other high voltage applications. Sourced from Process 48.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	300	V
V _{CBO}	Collector-Base Voltage	300	V
V _{EBO}	Emitter-Base Voltage	6.0	V
Ic	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		MPSA42	*MMBTA42	**PZTA42	-
P _D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/∘C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

NPN High Voltage Amplifier (continued)

Electrical (Characteristics	TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units

OFF CHARACTERISTICS

V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0$ mA, $I_{\rm B} = 0$	300		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	300		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \ \mu A, \ I_C = 0$	6.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 200 \text{ V}, I_E = 0$		0.1	μΑ
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 6.0 \text{ V}, I_{C} = 0$		0.1	μΑ

ON CHARACTERISTICS*

h _{FE}	DC Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$	25		
		$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	40		
		$I_{C} = 30 \text{ mA}, V_{CE} = 10 \text{ V}$	40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 20 \text{ mA}, I_{\rm B} = 2.0 \text{ mA}$		0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 20$ mA, $I_{\rm B} = 2.0$ mA		0.9	V

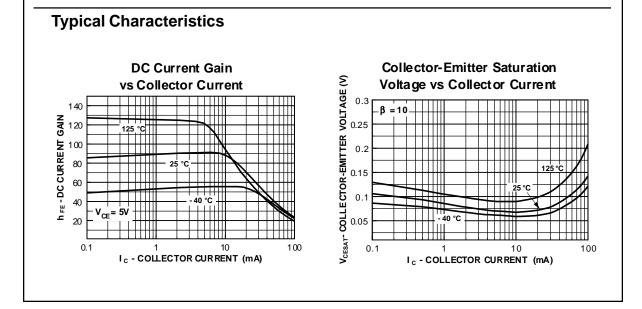
SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	50		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		3.0	pF

*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

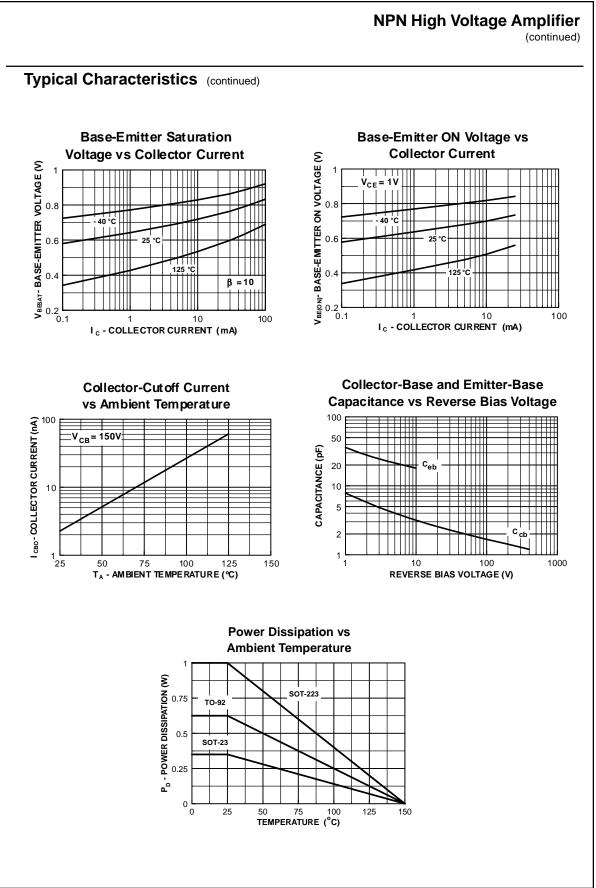
Spice Model

NPN (Is=34.9f Xti=3 Eg=1.11 Vaf=100 Bf=2.65K Ne=1.708 Ise=16.32p Ikf=23.79m Xtb=1.5 Br=9.769 Nc=2 Isc=0 Ikr=0 Rc=7 Cjc=14.23p Mjc=.5489 Vjc=.75 Fc=.5 Cje=49.62p Mje=.4136 Vje=.75 Tr=934.3p Tf=1.69n Itf=5 Vtf=20 Xtf=150 Rb=10)

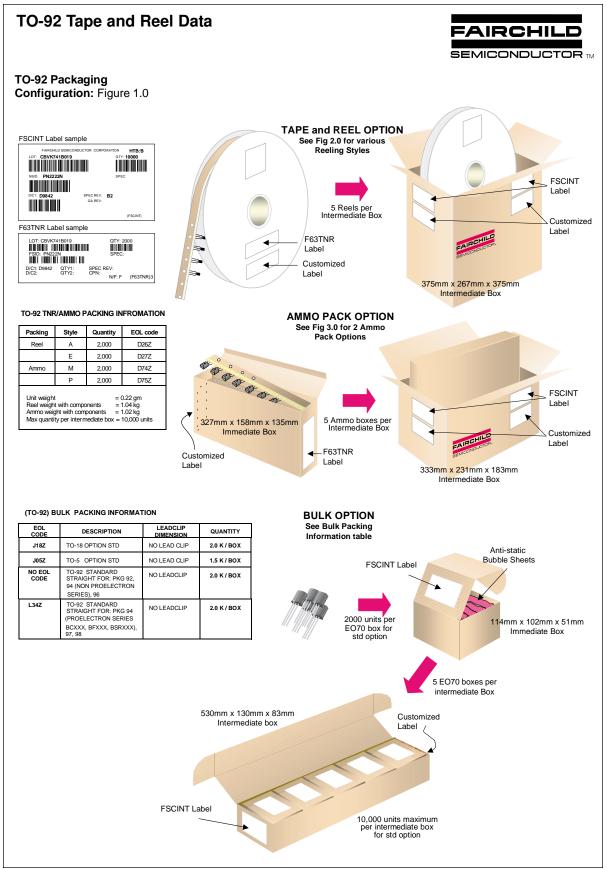


MPSA42 / MMBTA42 / PZTA42

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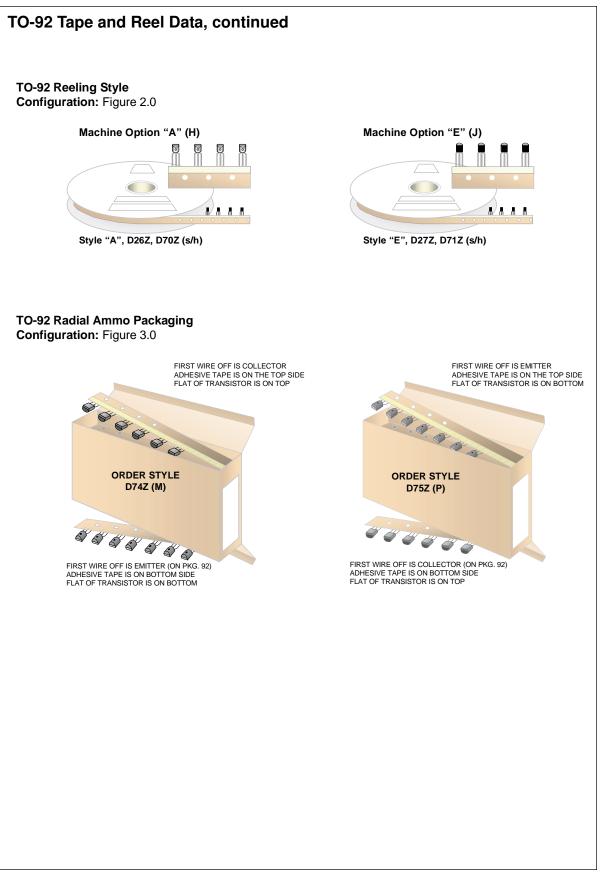


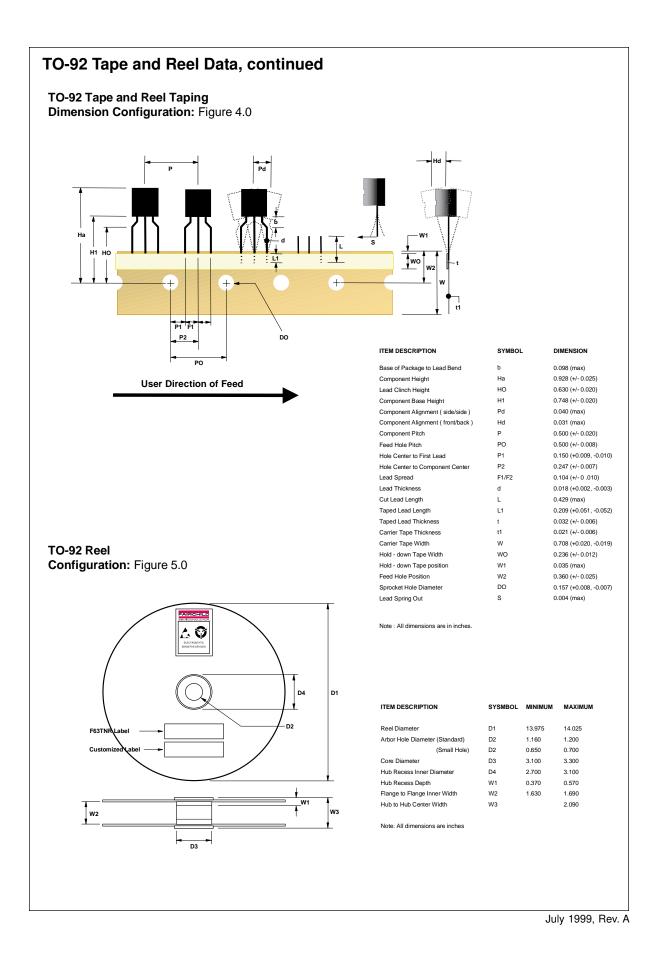
MPSA42 / MMBTA42 / PZTA42

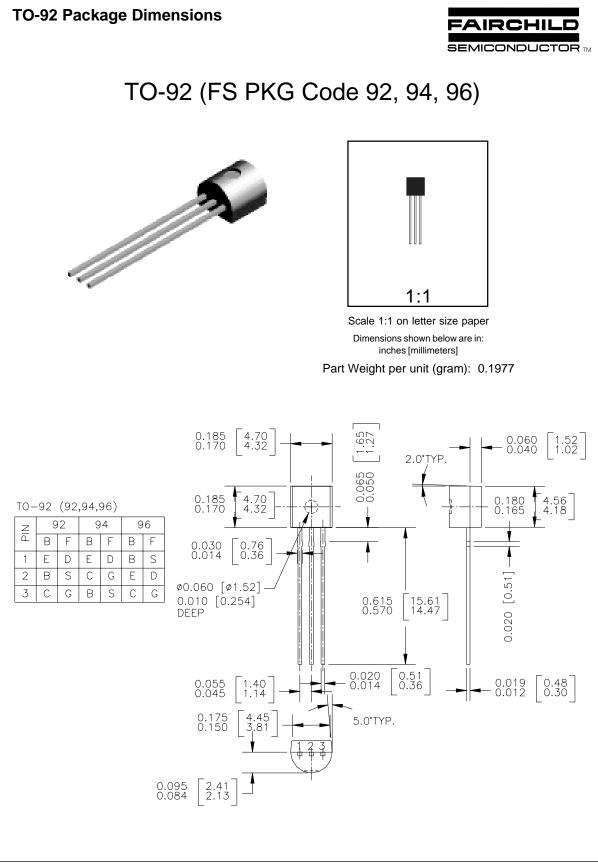


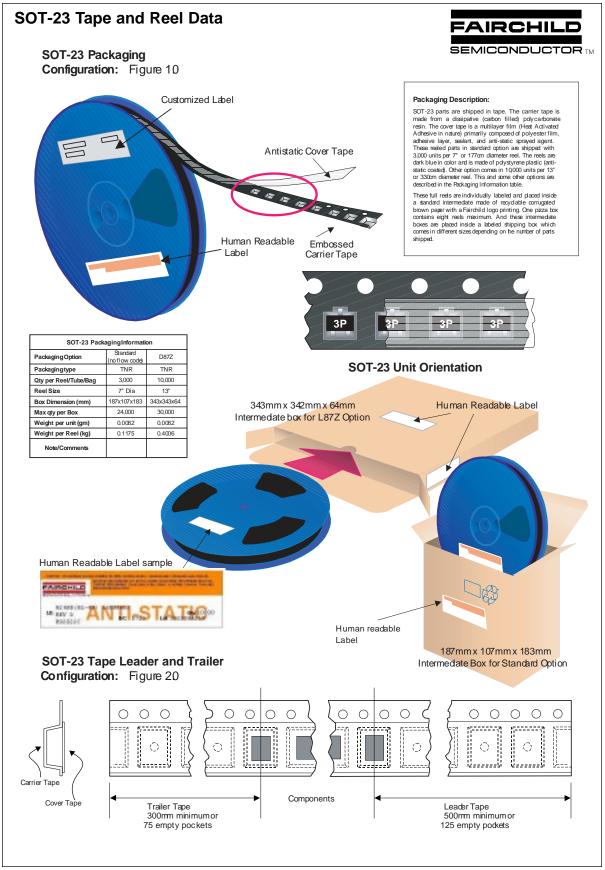
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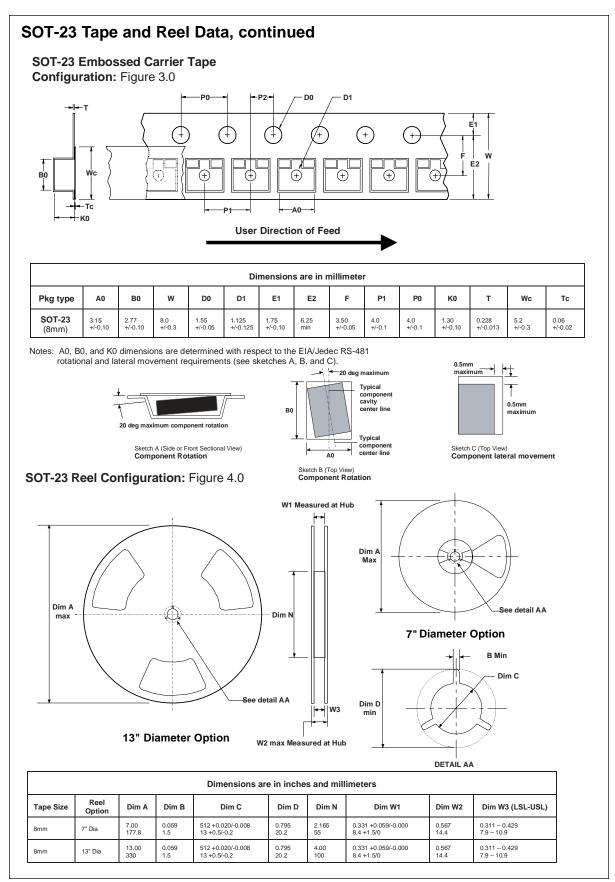




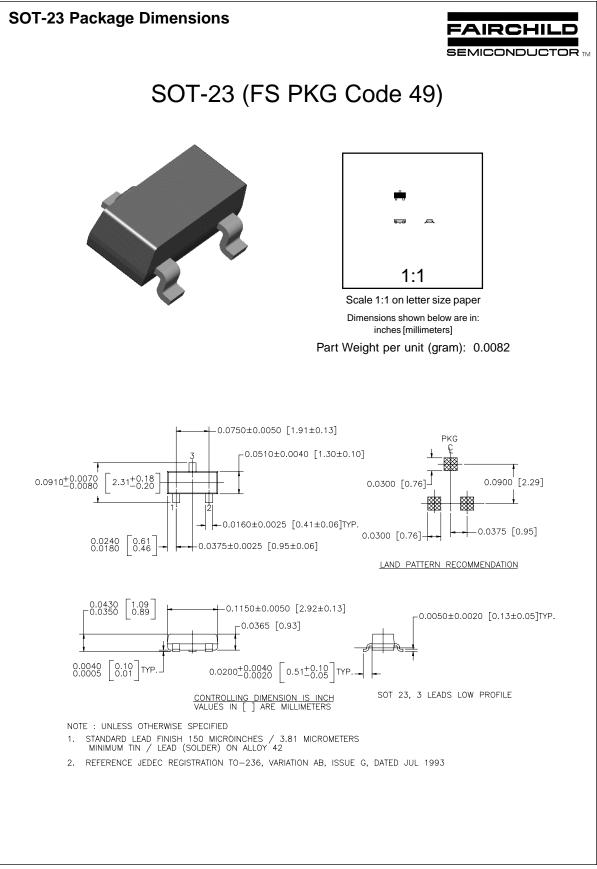


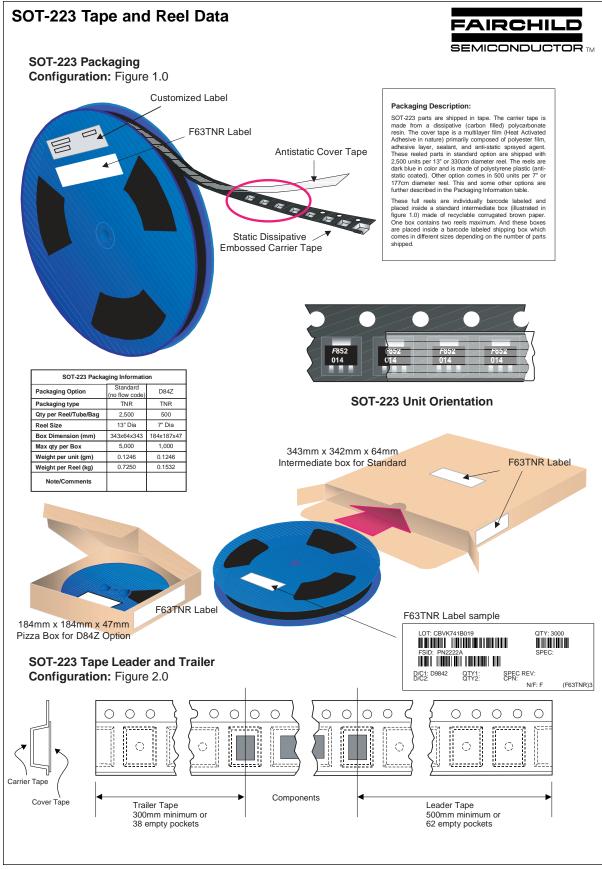
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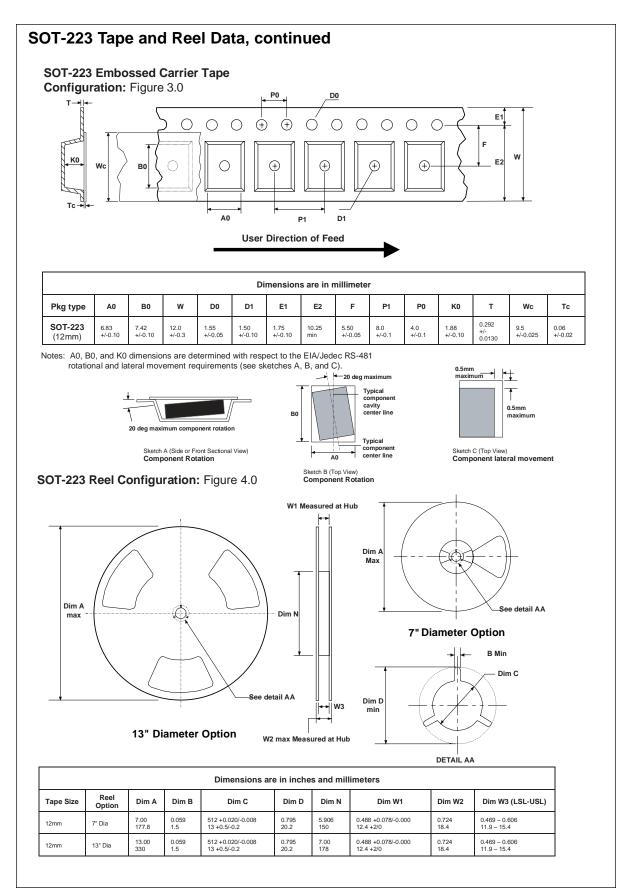
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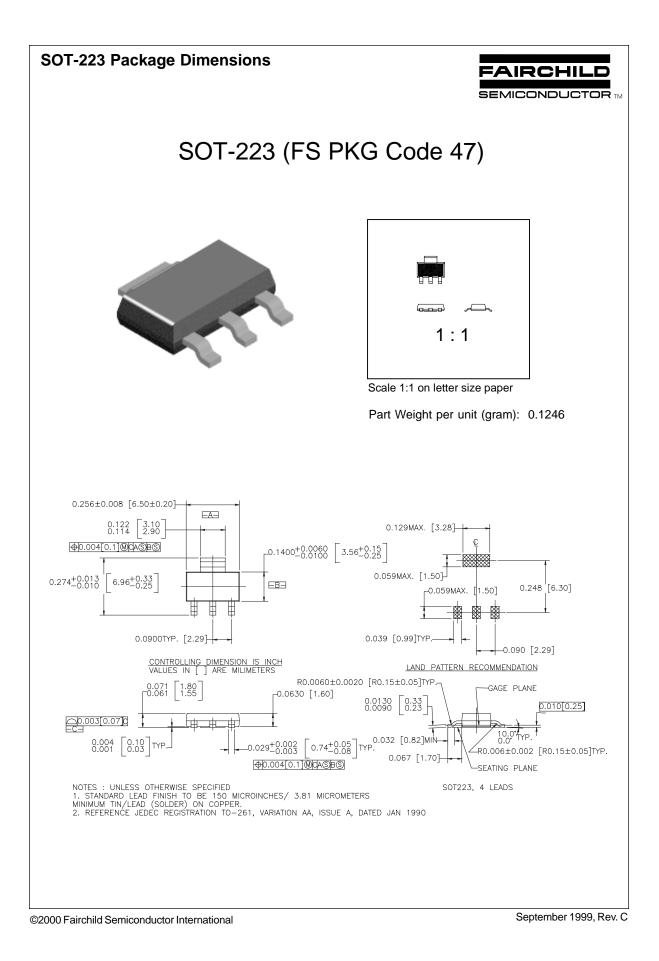




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